Vishay Semiconductors

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Hyperfast Rectifier, 75 A FRED Pt[®] G5



PRIMARY CHARACTERISTICS									
I _{F(AV)}	75 A								
V _R	600 V								
V _F at I _F at 125 °C	1.4 V								
t _{rr} (typ.)	29								
I _{FSM}	565								
T _J max.	175 °C								
Package	TO-247AD 2L								
Circuit configuration	Single								

FEATURES

- Hyperfast and optimized Qrr
- Best in class forward voltage drop and switching losses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature FREE
- Polyimide passivation
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for soft switched and resonant converters, as well as medium frequency hard switching converters. This device is specifically designed to improve efficiency of high speed LLC output rectification stages of EV / HEV battery charging stations and high frequency stages of UPS applications.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		600	V						
Average rectified forward current	I _{F(AV)}	T _C = 103 °C, D = 0.50	75							
Non-repetitive peak surge current	I _{FSM}	$T_C = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{ sine wave}$	565	А						
Repetitive peak forward current	I _{FRM}	T _C = 103 °C, D = 0.50, f = 20 kHz	150							
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	MIN.	TYP.	MAX.	UNITS					
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	600	-	-				
Ferryard valtage	M	I _F = 75 A	-	1.6	2.2	V			
Forward voltage	V _F	I _F = 75 A, T _J = 125 °C	-	1.4	-				
Deverse leakage eurrent	I _R	$V_{R} = V_{R}$ rated	-	-	25				
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA			
Junction capacitance	CT	V _R = 200 V	-	96	-	pF			
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH			

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COMPLIANT

HALOGEN

VS-E5PX7506L-N3



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 100$) A/µs, V _R = 30 V	-	29	-				
Reverse recovery time	t _{rr}	T _J = 25 °C		-	44	-	ns			
		T _J = 125 °C		-	69	-				
Peak recovery current		T _J = 25 °C	$I_F = 50 A$	-	18	-	A			
Feak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = 1000 A/µs V _B = 400 V	-	42	-				
	_	T _J = 25 °C		-	484	-	nC			
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1731	-				
	+	T _J = 25 °C		-	48	-				
Reverse recovery time	t _{rr}	T _J = 125 °C		-	75	-	ns			
Deale and a summark		T _J = 25 °C	$I_{\rm F} = 75 {\rm A}$	-	21	-	A			
Peak recovery current	I _{RRM}	T _J = 125 °C	dl _F /dt = 1000 A/µs V _B = 400 V	-	46	-				
2	0	T _J = 25 °C	1	-	573	-				
Reverse recovery charge	Q _{rr}	T _J = 125 °C	1	-	2048	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction-to-case	R _{thJC}		-	-	0.5	°C/W				
Woight			-	5.5	-	g				
Weight			-	0.2	-	oz.				
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Marking device		Case style: TO-247AD 2L	E5PX7506L							

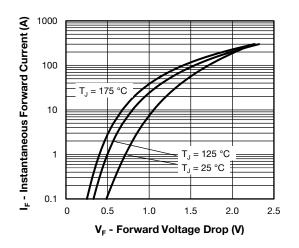


Fig. 1 - Forward Voltage Drop Characteristics, Per Leg

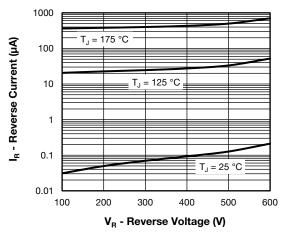


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage, Per Leg

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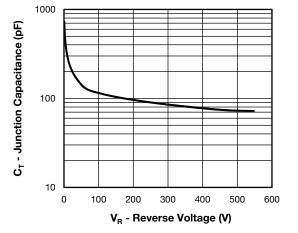


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage, Per Leg

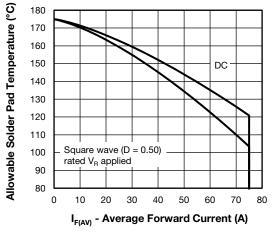


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current, Per Leg

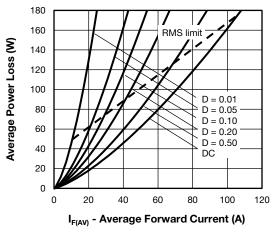


Fig. 5 - Forward Power Loss Characteristics, Per Leg

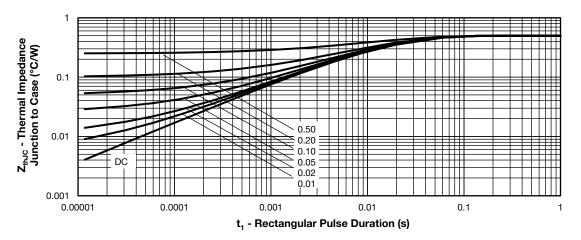


Fig. 6 - Transient Thermal Impedance, Junction to Case, Per Leg

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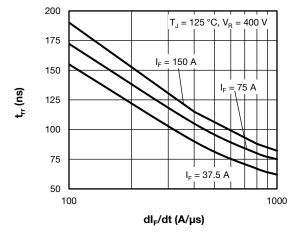


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt, Per Leg

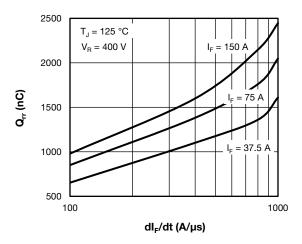


Fig. 8 - Typical Reverse Recovery Charge vs. dl_F/dt, Per Leg

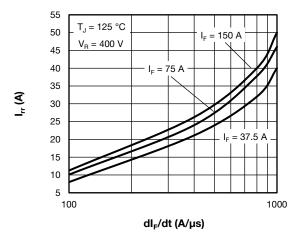


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt, Per Leg

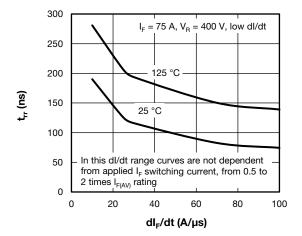


Fig. 10 - Typical Reverse Recovery Time vs. dl_F/dt, Per Leg

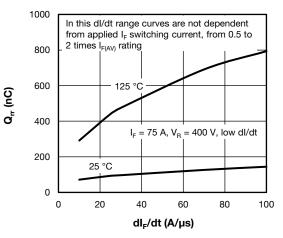


Fig. 11 - Typical Reverse Recovery Charge vs. dl_F/dt, Per Leg

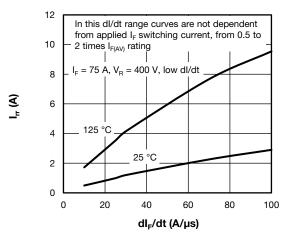


Fig. 12 - Typical Reverse Recovery Current vs. dl_F/dt, Per Leg

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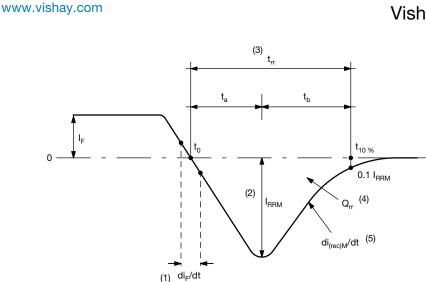


Fig. 13 - Reverse Recovery Waveform and Definitions

Notes

- $^{(1)}~di_{F}/dt$ rate of change of current through zero crossing
- ⁽²⁾ I_{RRM} peak reverse recovery current ⁽³⁾ t_{rr} reverse recovery time measured from t_0 , crossing point of negative going I_F , to point $t_{10\%}$, 0.1 I_{RRM}
- $^{(4)}$ \dot{Q}_{rr} area under curve defined by t_0 and $t_{10\ \%}$

$$Q_{rr} = \int_{t_0}^{t_{10} \%} I(t) dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE

Device code	VS-	Е	5	Р	x	75	06	L	-N3	
	1	2	3	4	5	6	7	8	9	
	1 - Vishay Semiconductors product									
	2 - E = single diode									
	3 -	3 - 5 = Fred generation 5								
	4 -	Pac	kage:							
		P =	TO-247	packag	e					
	5 -	X =	hyperfa	st recov	ery					
	6 -	Cur	rent rati	ng (75 =	= 75 A)					
	7 -	7 - Voltage rating (06 = 600 V)								
	8 -	8 - Package: L = long lead (TO-247AD)								
	9 -									
	لئے	-N3	= halog	gen-free	, RoHS-	complia	ant, and	totally I	ead (Pb)	

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-E5PX7506L-N3	25	500	Antistatic plastic tube						
		•							

LINKS TO RELATED DOCUMENTS Dimensions www.vishay.com/doc?95536 Part marking information www.vishay.com/doc?95648

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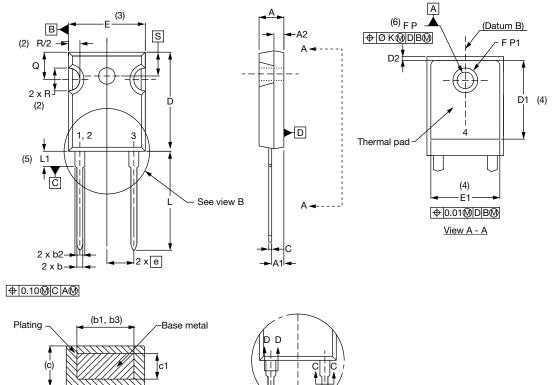
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TO-247AD 2L

DIMENSIONS in millimeters and inches



Section C - C, D - D

(b, b2)

(4)

View	<u>/ B</u>

SYMBOL	MILLIN	IETERS	INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES	
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STMDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209			E	15.29	15.87	0.602	0.625	3
A1	2.21	2.59	0.087	0.102			E1	13.46	-	0.53	-	
A2	1.50	2.49	0.059	0.098			е	5.46	BSC	0.215	5 BSC	
b	0.99	1.40	0.039	0.055			ØК	0.2	254	0.0	010	
b1	0.99	1.35	0.039	0.053			L	19.81	20.32	0.780	0.800	
b2	1.65	2.39	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b3	1.65	2.34	0.065	0.092			ØР	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	6.98	-	0.275	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	' BSC	
D2	0.51	1.35	0.020	0.053				•		•		•

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

(5) Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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